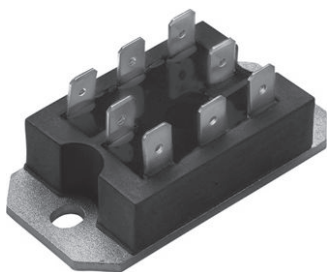


Power Modules, Passivated Assembled Circuit Elements, 40 A


PACE-PAK (D-19)

FEATURES

- Glass passivated junctions for greater reliability
- Electrically isolated base plate
- Available up to 1200 V_{RRM}/V_{DRM}
- High dynamic characteristics
- Wide choice of circuit configurations
- Simplified mechanical design and assembly
- UL E78996 approved 
- Material categorization: For definitions of compliance please see www.vishay.com/doc?99912


RoHS
COMPLIANT

PRODUCT SUMMARY

I_O	40 A
Type	Modules - Thyristor, Standard
Package	PACE-PAK (D-19)
Circuit	Single phase, hybrid bridge common cathode, Single phase, hybrid bridge doubler connection, Single phase, all SCR bridge

DESCRIPTION

The VS-P400 series of integrated power circuits consists of power thyristors and power diodes configured in a single package. With its isolating base plate, mechanical designs are greatly simplified giving advantages of cost reduction and reduced size.

Applications include power supplies, control circuits and battery chargers.

MAJOR RATINGS AND CHARACTERISTICS

SYMBOL	CHARACTERISTICS	VALUES	UNITS
I_O	80 °C	40	A
I_{TSM} , I_{FSM}	50 Hz 60 Hz	385 400	A
I^2t	50 Hz 60 Hz	745 680	A ² s
$I^2\sqrt{t}$		7450	A ² √s
V_{RRM}	Range	400 to 1200	V
V_{ISOL}		2500	V
T_J T_{Stg}		-40 to 125	°C

ELECTRICAL SPECIFICATIONS

VOLTAGE RATINGS

TYPE NUMBER	V_{RRM}/V_{DRM} , MAXIMUM REPETITIVE PEAK REVERSE AND PEAK OFF-STATE VOLTAGE V	V_{RSM} , MAXIMUM NON-REPETITIVE PEAK REVERSE VOLTAGE V	I_{RRM} MAXIMUM AT T_J MAXIMUM mA
VS-P401, VS-P421, VS-P431	400	500	10
VS-P402, VS-P422, VS-P432	600	700	
VS-P403, VS-P423, VS-P433	800	900	
VS-P404, VS-P424, VS-P434	1000	1100	
VS-P405, VS-P425, VS-P435	1200	1300	



ON-STATE CONDUCTION						
PARAMETER	SYMBOL	TEST CONDITIONS			VALUES	UNITS
Maximum DC output current at case temperature	I _O	Full bridge circuits			40	A
					80	°C
Maximum peak, one-cycle non-repetitive on-state or forward current	I _{TSM} , I _{FSM}	t = 10 ms	No voltage reapplied	Sinusoidal half wave, initial T _J = T _J maximum	385	A
		t = 8.3 ms			400	
		t = 10 ms	100 % V _{RRM} reapplied		325	
		t = 8.3 ms			340	
Maximum I ² t for fusing	I ² t	t = 10 ms	No voltage reapplied		745	A ² s
		t = 8.3 ms			680	
		t = 10 ms	100 % V _{RRM} reapplied		530	
		t = 8.3 ms			480	
Maximum I ² √t for fusing	I ² √t	t = 0.1 ms to 10 ms, no voltage reapplied I ² t for time tx = I ² √t · √tx			7450	A ² √s
Low level value of threshold voltage	V _{T(TO)1}	(16.7 % x π x I _{T(AV)}) < I < π x I _{T(AV)} , T _J = T _J maximum			0.83	V
High level value of threshold voltage	V _{T(TO)2}	(I > π x I _{T(AV)}), T _J = T _J maximum			1.03	
Low level value of on-state slope resistance	r _{t1}	(16.7 % x π x I _{T(AV)}) < I < π x I _{T(AV)} , T _J = T _J maximum			9.61	mΩ
High level value of on-state slope resistance	r _{t2}	(I > π x I _{T(AV)}), T _J = T _J maximum			7.01	
Maximum on-state voltage drop	V _{TM}	I _{TM} = π x I _{T(AV)}		T _J = 25 °C	1.4	V
Maximum forward voltage drop	V _{FM}	I _{FM} = π x I _{F(AV)}		T _J = 25 °C	1.4	V
Maximum non-repetitive rate of rise of turned-on current	di/dt	T _J = 125 °C from 0.67 V _{DRM} I _{TM} = π x I _{T(AV)} , I _g = 500 mA, t _r < 0.5 μs, t _p > 6 μs			200	A/μs
Maximum holding current	I _H	T _J = 25 °C anode supply = 6 V, resistive load			130	mA
Maximum latching current	I _L				250	

BLOCKING				
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Maximum critical rate of rise of off-state voltage	dV/dt	T _J = 125 °C, exponential to 0.67 V _{DRM} gate open	200	V/μs
Maximum peak reverse and off-state leakage current at V _{RRM} , V _{DRM}	I _{RRM} , I _{DRM}	T _J = 125 °C, gate open circuit	10	mA
Maximum peak reverse leakage current	I _{RRM}	T _J = 25 °C	100	μA
RMS isolation voltage	V _{ISOL}	50 Hz, circuit to base, all terminals shorted, T _J = 25 °C, t = 1 s	2500	V

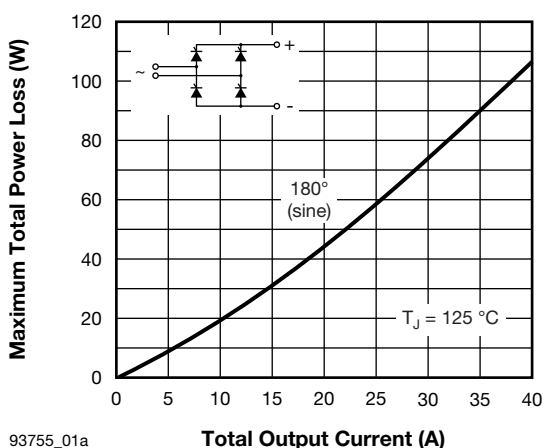
TRIGGERING						
PARAMETER	SYMBOL	TEST CONDITIONS		VALUES	UNITS	
Maximum peak gate power	P _{GM}			8	W	
Maximum average gate power	P _{G(AV)}			2		
Maximum peak gate current	I _{GM}			2	A	
Maximum peak negative gate voltage	-V _{GM}			10	V	
Maximum gate voltage required to trigger	V _{GT}	T _J = - 40 °C	Anode supply = 6 V resistive load	3	V	
		T _J = 25 °C		2		
		T _J = 125 °C		1		
Maximum gate current required to trigger	I _{GT}	T _J = - 40 °C		90	mA	
		T _J = 25 °C		60		
		T _J = 125 °C		35		
Maximum gate voltage that will not trigger	V _{GD}	T _J = 125 °C, rated V _{DRM} applied		0.2	V	
Maximum gate current that will not trigger	I _{GD}			2	mA	



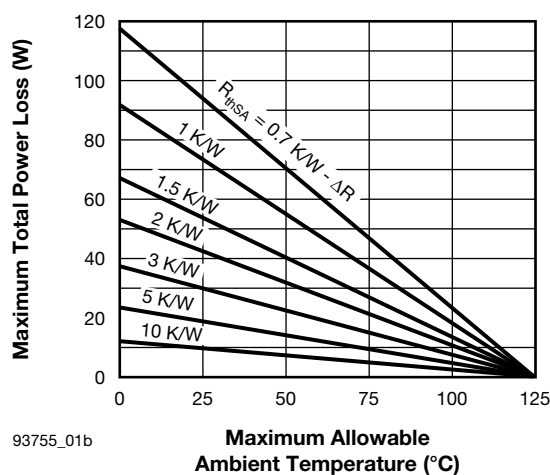
THERMAL AND MECHANICAL SPECIFICATIONS				
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Maximum junction operating and storage temperature range	T_J, T_{Stg}		-40 to 125	°C
Maximum thermal resistance, junction to case per junction	R_{thJC}	DC operation	1.05	K/W
Maximum thermal resistance, case to heatsink	R_{thCS}	Mounting surface, smooth and greased	0.10	
Mounting torque, base to heatsink ⁽¹⁾			4	Nm
Approximate weight			58	g
			2.0	oz.
Case style			PACE-PAK (D-19)	

Note

⁽¹⁾ A mounting compound is recommended and the torque should be checked after a period of 3 hours to allow for the spread of the compound

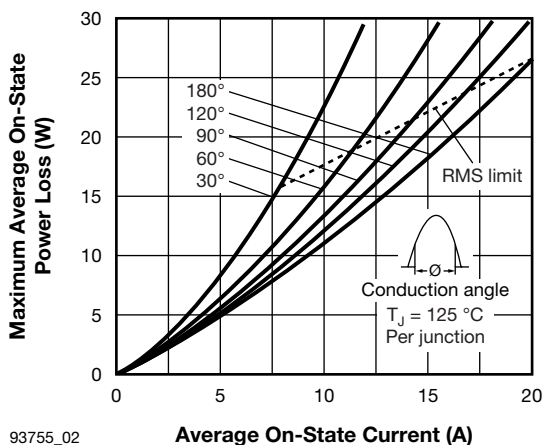


93755_01a



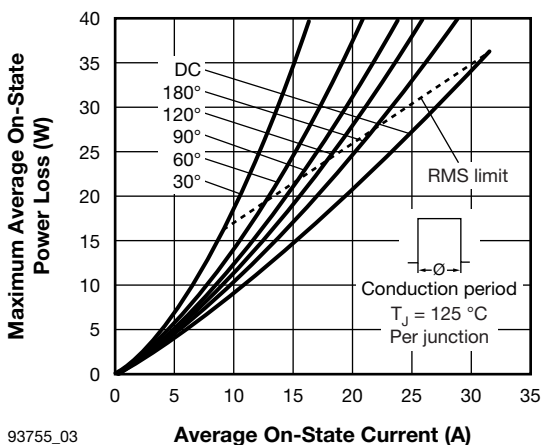
93755_01b

Fig. 1 - Current Ratings Nomogram (1 Module Per Heatsink)



93755_02

Fig. 2 - On-State Power Loss Characteristics



93755_03

Fig. 3 - On-State Power Loss Characteristics

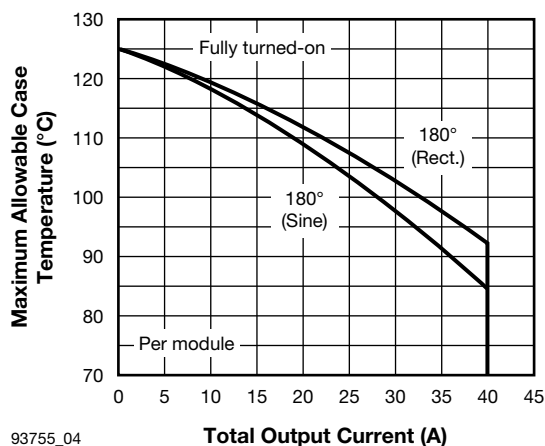


Fig. 4 - Current Ratings Characteristics

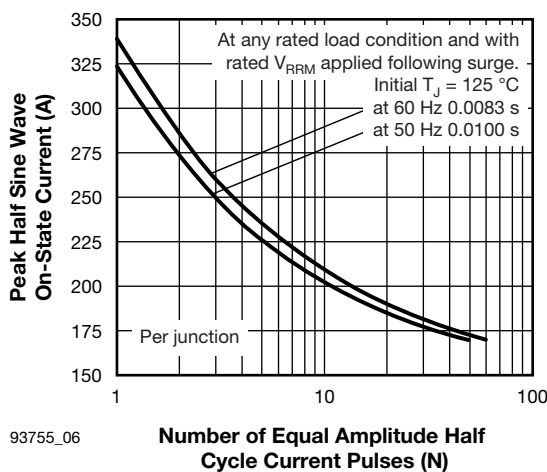


Fig. 6 - Maximum Non-Repetitive Surge Current

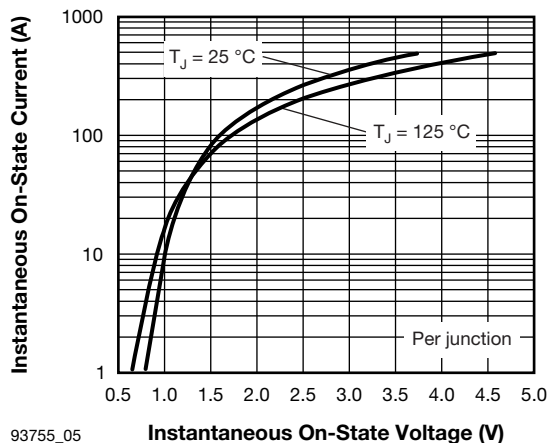


Fig. 5 - On-State Voltage Drop Characteristics

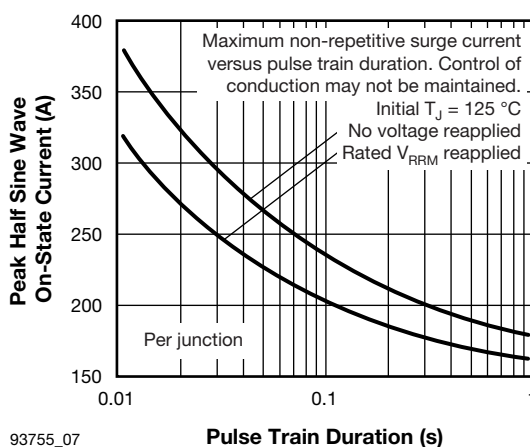
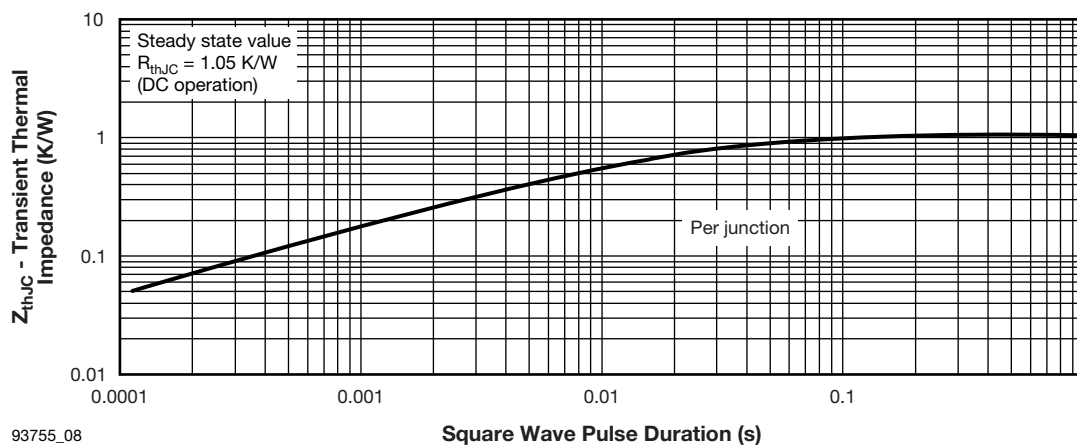


Fig. 7 - Maximum Non-Repetitive Surge Current


Fig. 8 - Thermal Impedance Z_{thJC} Characteristics

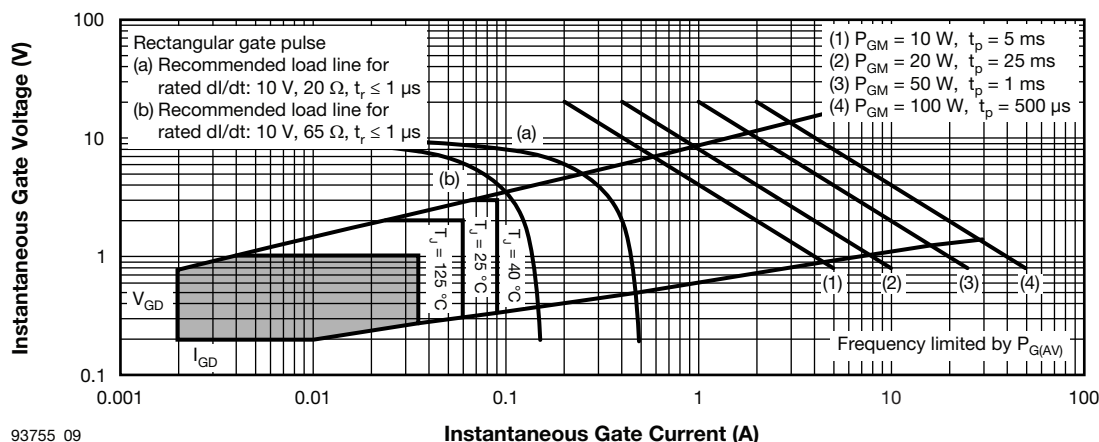
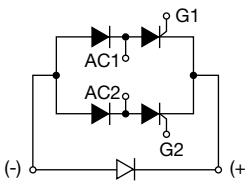
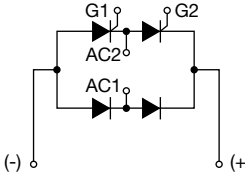
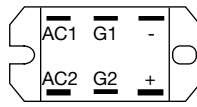
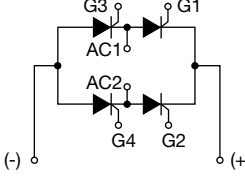
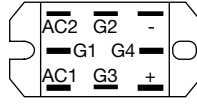


Fig. 9 - Gate Characteristics

ORDERING INFORMATION TABLE

Device code	VS-	P	4	0	2	K	W
	1	2	3	4	5	6	7
1	-	Vishay Semiconductors product					
2	-	Module type					
3	-	Current rating					
		1 = 25 A DC (P100 Series)					
		4 = 40 A DC (P400 Series)					
4	-	Circuit configuration					
		0 = Single Phase, Hybrid Bridge Common Cathode					
		2 = Single Phase, Hybrid Bridge Doubler Connection					
		3 = Single Phase, all SCR Bridge					
5	-	Voltage code					
		1 = 400 V					
		2 = 600 V					
		3 = 800 V					
		4 = 1000 V					
		5 = 1200 V					
6	-	K = Optional Voltage Suppression					
7	-	W = Optional Freewheeling Diode					

CIRCUIT CONFIGURATION			
CIRCUIT DESCRIPTION	CIRCUIT CONFIGURATION CODE	SCHEMATIC DIAGRAM	TERMINAL POSITIONS
Single phase, hybrid bridge common cathode	0		
Single phase, hybrid bridge doubler connection	2		
Single phase, all SCR bridge	3		

CODING (1)					
CIRCUIT DESCRIPTION	CIRCUIT CONFIGURATION CODE	BASIC SERIES	WITH VOLTAGE SUPPRESSION	WITH FREEWHEELING DIODE	WITH BOTH VOLTAGE SUPPRESSION AND FREEWHEELING DIODE
Single phase, hybrid bridge common cathode	0	P40.	P40.K	P40.W	P40.KW
Single phase, hybrid bridge doubler connection	2	P42.	P42.K	-	-
Single phase, all SCR bridge	3	P43.	P43.K	-	-

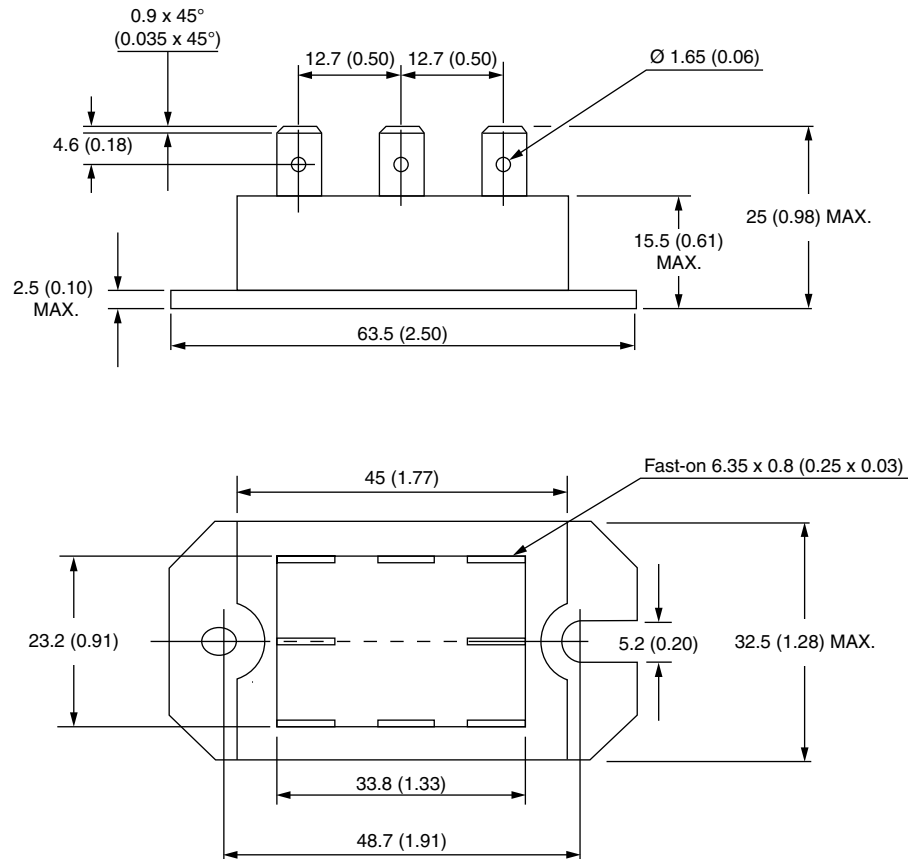
Note

(1) To complete code refer to Voltage Ratings table, i.e.: For 600 V P40.W complete code is P402W

LINKS TO RELATED DOCUMENTS	
Dimensions	www.vishay.com/doc?95335

D-19 PACE-PAK

DIMENSIONS in millimeters (inches)





Disclaimer

ALL PRODUCT, PRODUCT SPECIFICATIONS AND DATA ARE SUBJECT TO CHANGE WITHOUT NOTICE TO IMPROVE RELIABILITY, FUNCTION OR DESIGN OR OTHERWISE.

Vishay Intertechnology, Inc., its affiliates, agents, and employees, and all persons acting on its or their behalf (collectively, "Vishay"), disclaim any and all liability for any errors, inaccuracies or incompleteness contained in any datasheet or in any other disclosure relating to any product.

Vishay makes no warranty, representation or guarantee regarding the suitability of the products for any particular purpose or the continuing production of any product. To the maximum extent permitted by applicable law, Vishay disclaims (i) any and all liability arising out of the application or use of any product, (ii) any and all liability, including without limitation special, consequential or incidental damages, and (iii) any and all implied warranties, including warranties of fitness for particular purpose, non-infringement and merchantability.

Statements regarding the suitability of products for certain types of applications are based on Vishay's knowledge of typical requirements that are often placed on Vishay products in generic applications. Such statements are not binding statements about the suitability of products for a particular application. It is the customer's responsibility to validate that a particular product with the properties described in the product specification is suitable for use in a particular application. Parameters provided in datasheets and / or specifications may vary in different applications and performance may vary over time. All operating parameters, including typical parameters, must be validated for each customer application by the customer's technical experts. Product specifications do not expand or otherwise modify Vishay's terms and conditions of purchase, including but not limited to the warranty expressed therein.

Except as expressly indicated in writing, Vishay products are not designed for use in medical, life-saving, or life-sustaining applications or for any other application in which the failure of the Vishay product could result in personal injury or death. Customers using or selling Vishay products not expressly indicated for use in such applications do so at their own risk. Please contact authorized Vishay personnel to obtain written terms and conditions regarding products designed for such applications.

No license, express or implied, by estoppel or otherwise, to any intellectual property rights is granted by this document or by any conduct of Vishay. Product names and markings noted herein may be trademarks of their respective owners.